

Microfabrication of TES microcalorimeters for the HOLMES experiment



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HOLMES is an experiment aiming at pushing down the sensitivity on the smallest neutrino mass at the order of \sim eV performing a calorimetric measurement of the Electron Capture decay spectrum of ^{163}Ho . For reaching its goal, HOLMES will deploy an array of 1000 microcalorimeters based on Transition Edge Sensors with gold absorbers in which the ^{163}Ho will be ion implanted. A major challenge is represented by the fabrication of the microcalorimeters with the required amount of ^{163}Ho (300 Hz/det). Therefore, the fabrication process needs to be compatible with ion implantation without impairing the detector performances. The gold absorber will be fabricated in more steps: before, during and after the ion implantation. In particular, the gold deposition during the embedding process is intended to compensate for the absorber atom sputtering caused by ion implantation and to control the ^{163}Ho concentration in the detectors. The implanted area will finally be encapsulated in-situ to ensure the fully containment of the decay energy and to avoid oxidation of the holmium. We describe here the multi-step microfabrication process, mainly focusing on the last steps..

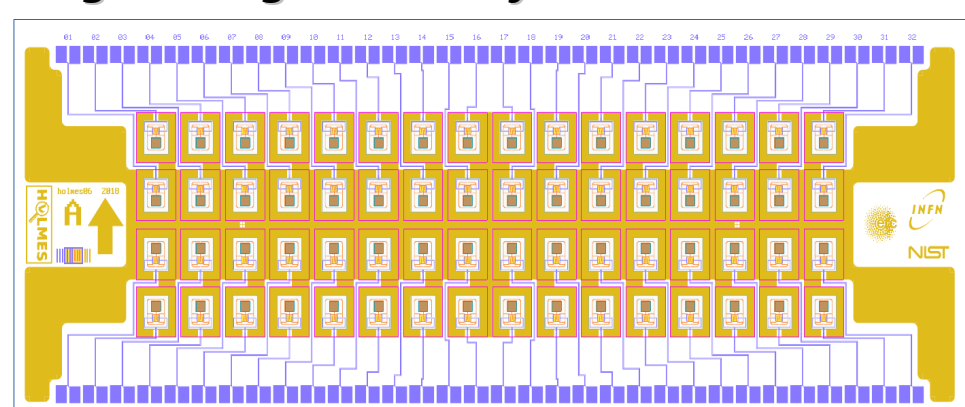
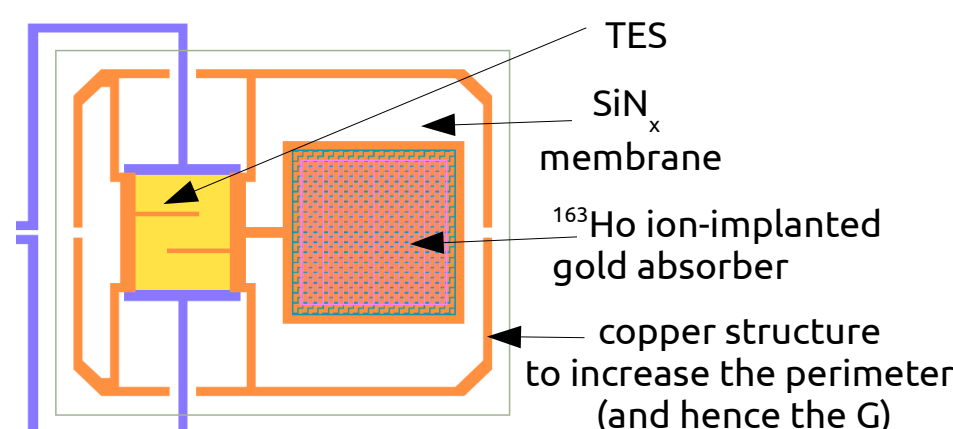
Detector design

Detectors: Transition Edge Sensor (TES) with ^{163}Ho implanted in Au absorbers

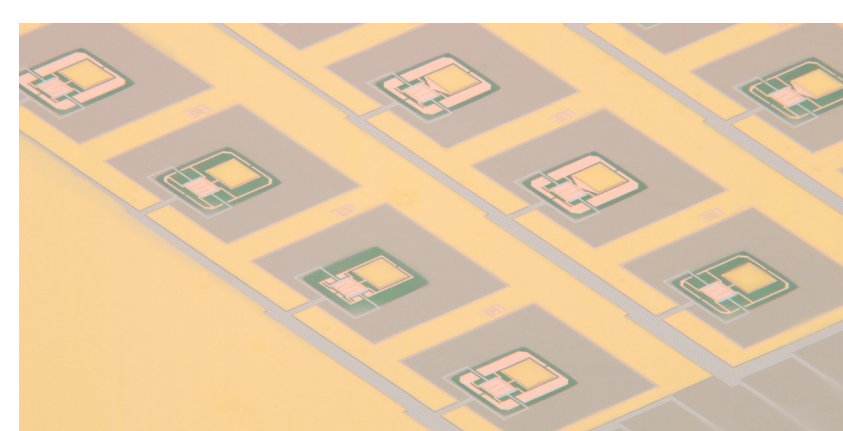
Activity: 6.5×10^{13} nuclei per detector
→ 300 dec/s

Performances: $\Delta E \approx 1$ eV and $\tau_r \approx 1$ μ s

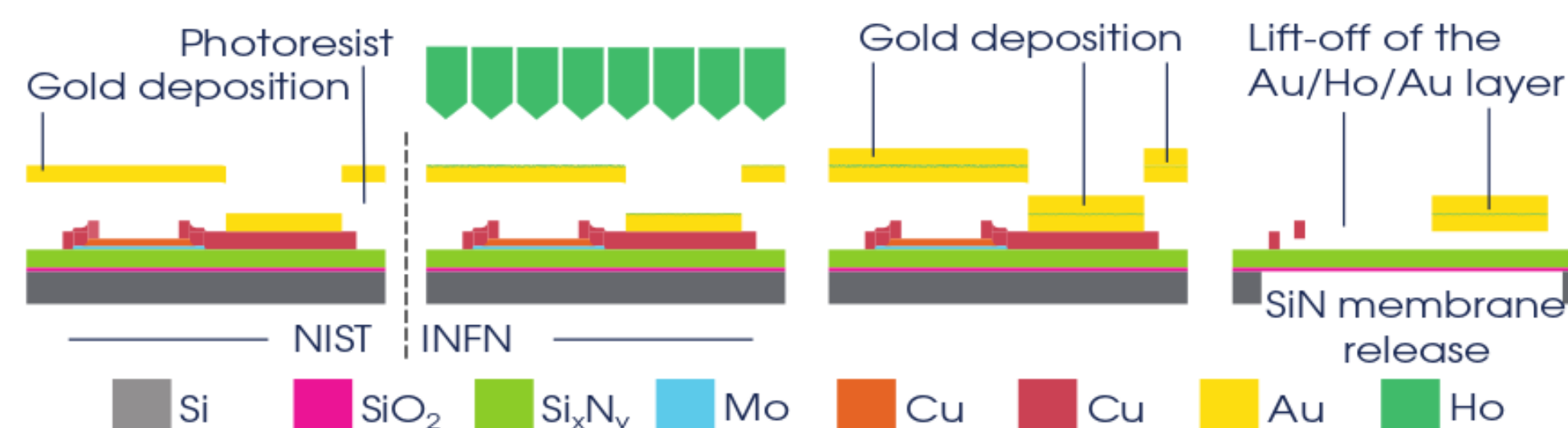
Design: side-car design to avoid TES proximity and G engineering for τ decay control



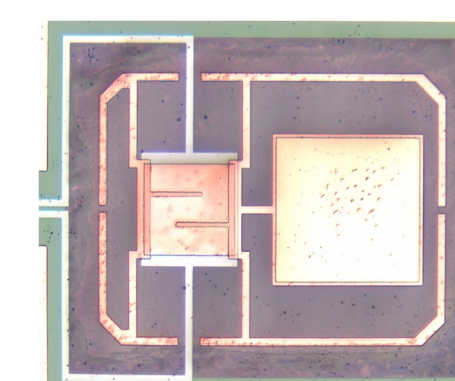
4 x 16 linear sub-array
for low parasitic L and
high implant efficiency
7x19 mm in size



Detector array fabrication

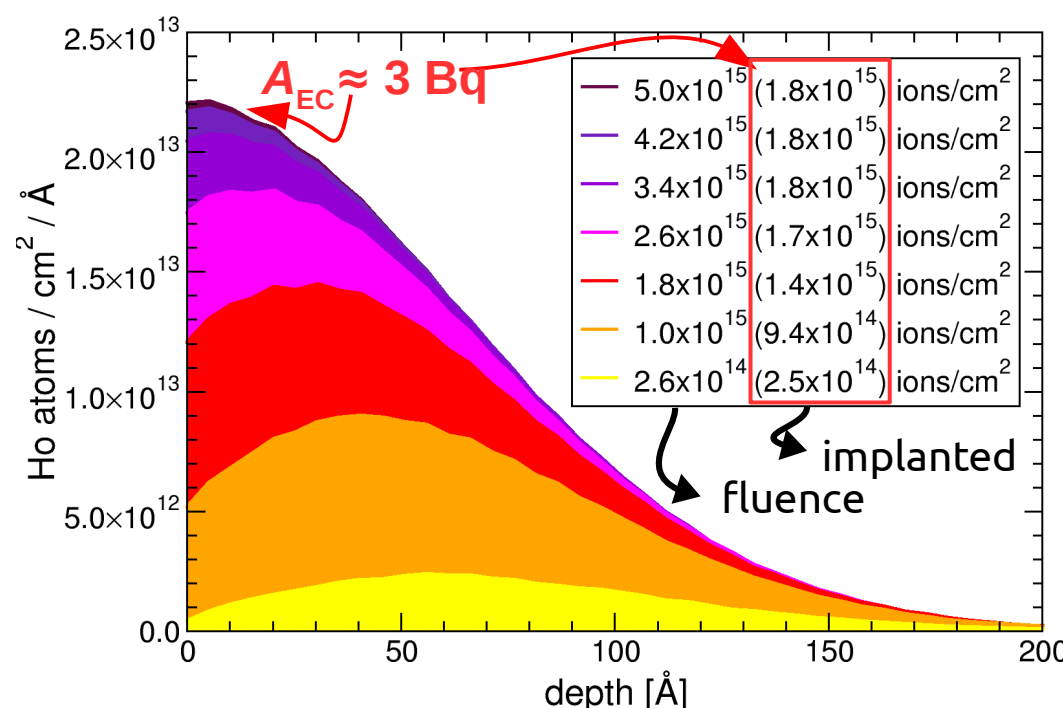


- TES originally fabricated at NIST, Boulder, CO, USA
- ^{163}Ho implantation and final 1 μ m Au layer deposition at INFN, Genova, Italy
- final fabrication processes: SiN membrane release & lift-off

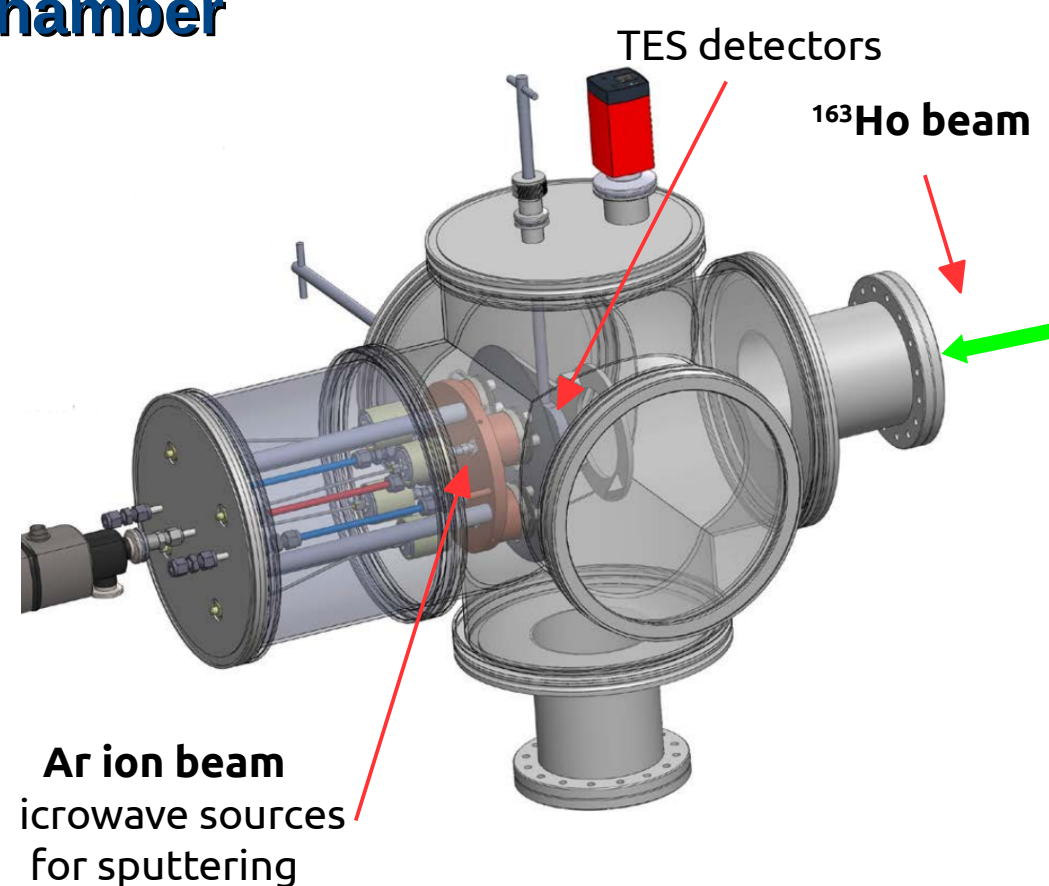


Target Chamber

ion implant simulation with SRIM2013
 ^{163}Ho ions on Au ($E_{ion} = 50$ keV)



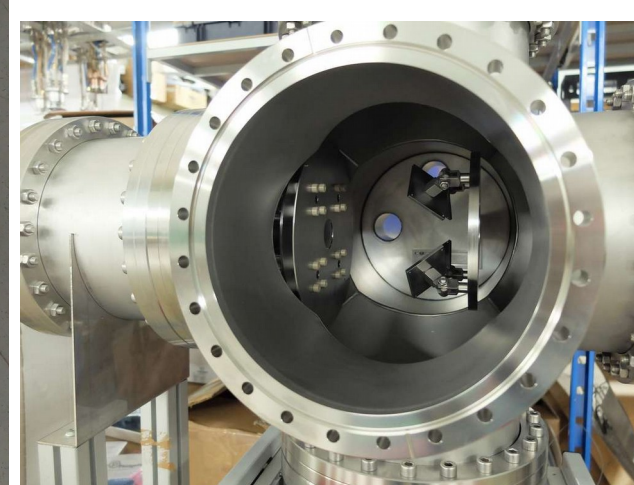
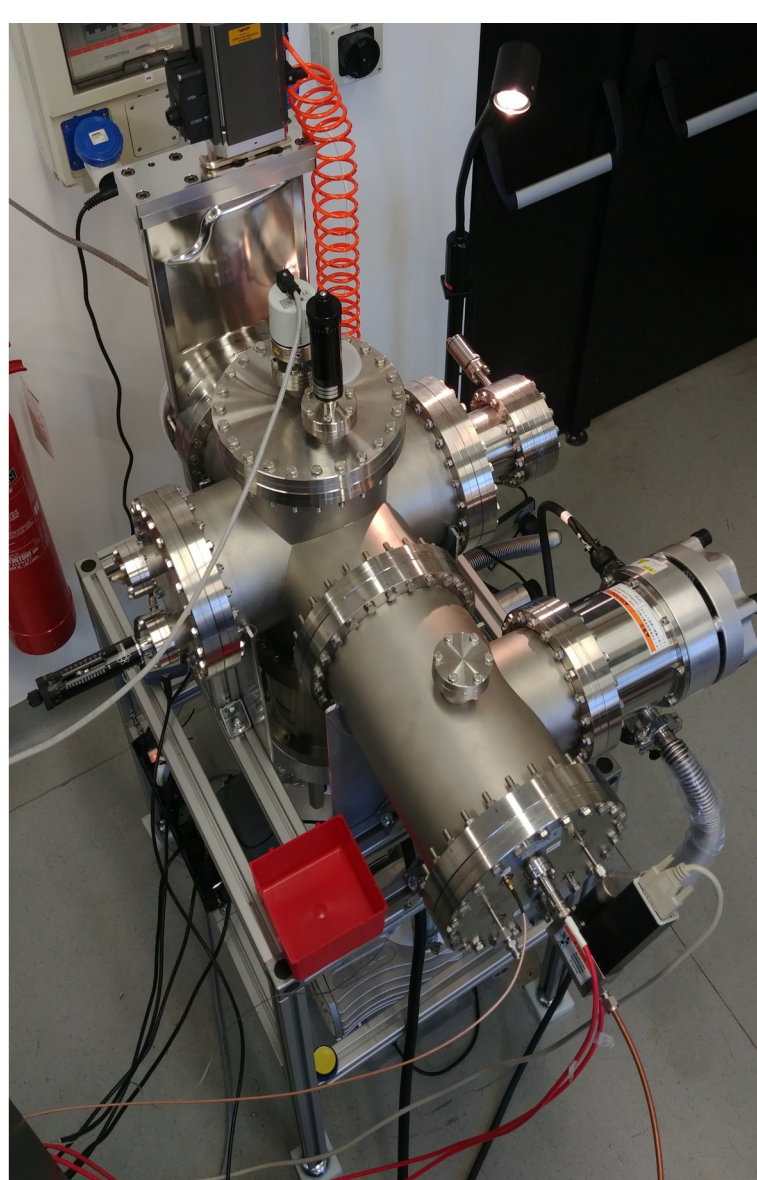
- ^{163}Ho concentration in absorbers saturate because ^{163}Ho sputters off Au from absorber
- effect compensated by Au co-evaporation (also for heat capacity reasons)
- final 1 μ m Au layer deposited in situ to avoid oxidation



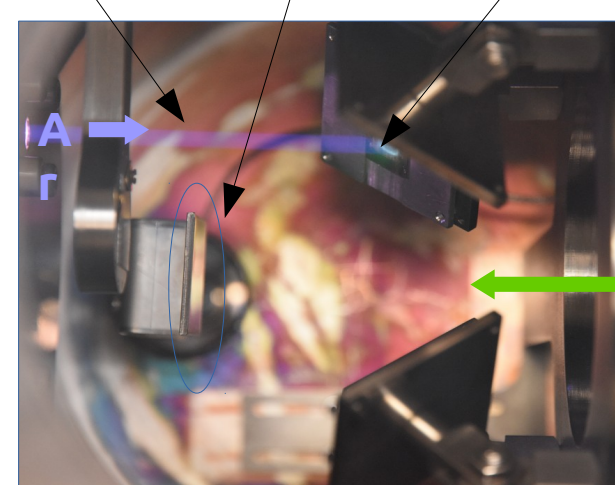
Ar ion beam
microwave sources
for sputtering

Ion Beam sputter system for on-line deposition

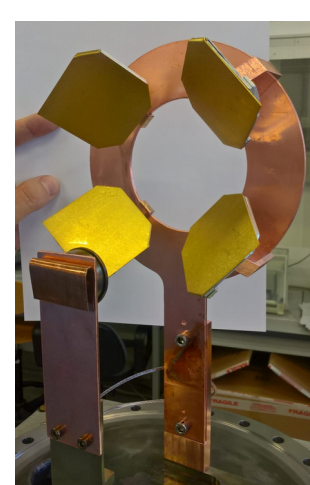
- 4 ECR ion beam sources
- Testing/optimization in progress with 4 ECR sources
→ Au deposition rate control and maximization
→ Au film quality and uniformity characterization
- Deposition rate \approx 50nm/h



TES holder
Argon beam



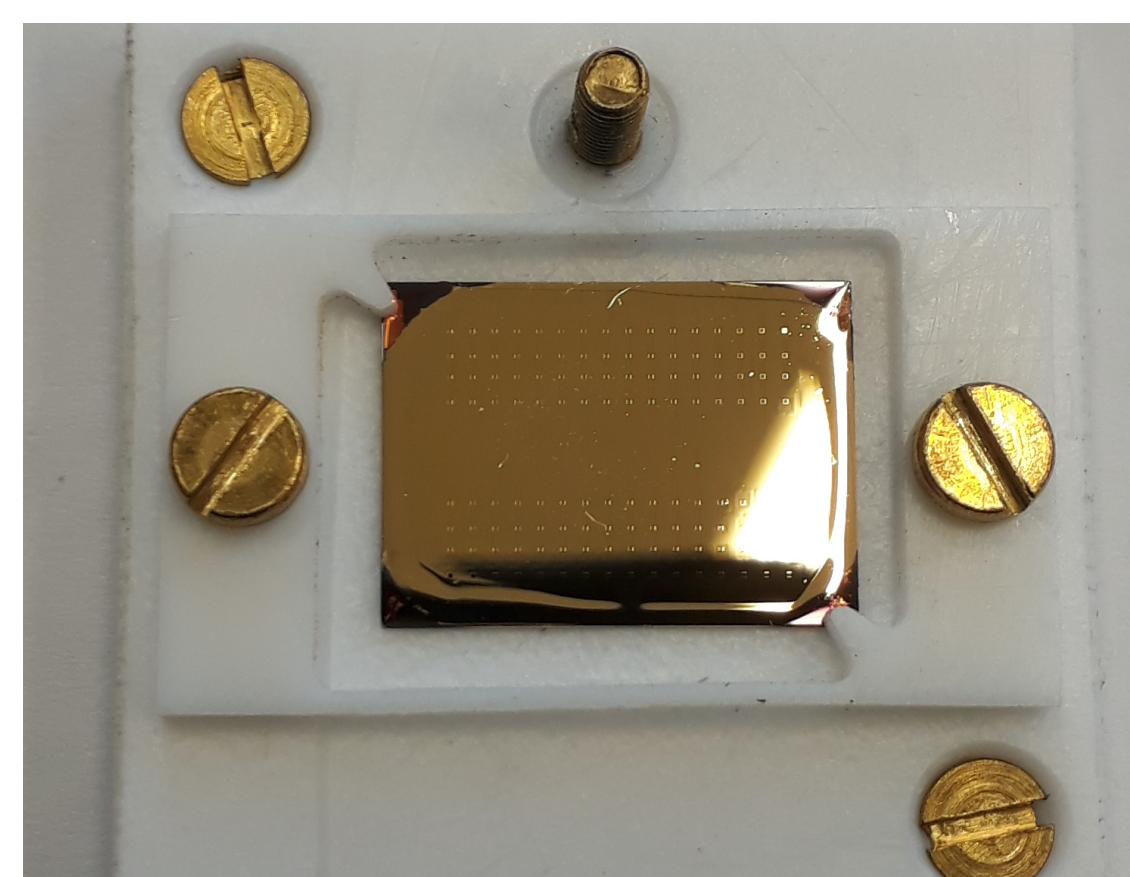
4 Au
targets



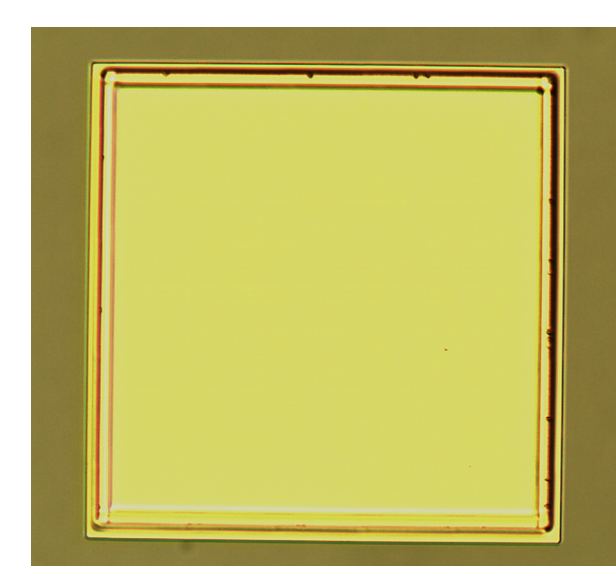
Lift off step

Patterning of Gold Absorber

Deposition of 1 μ m of Au (\sim 20 h)
Photoresist mask \rightarrow 7 μ m thickness



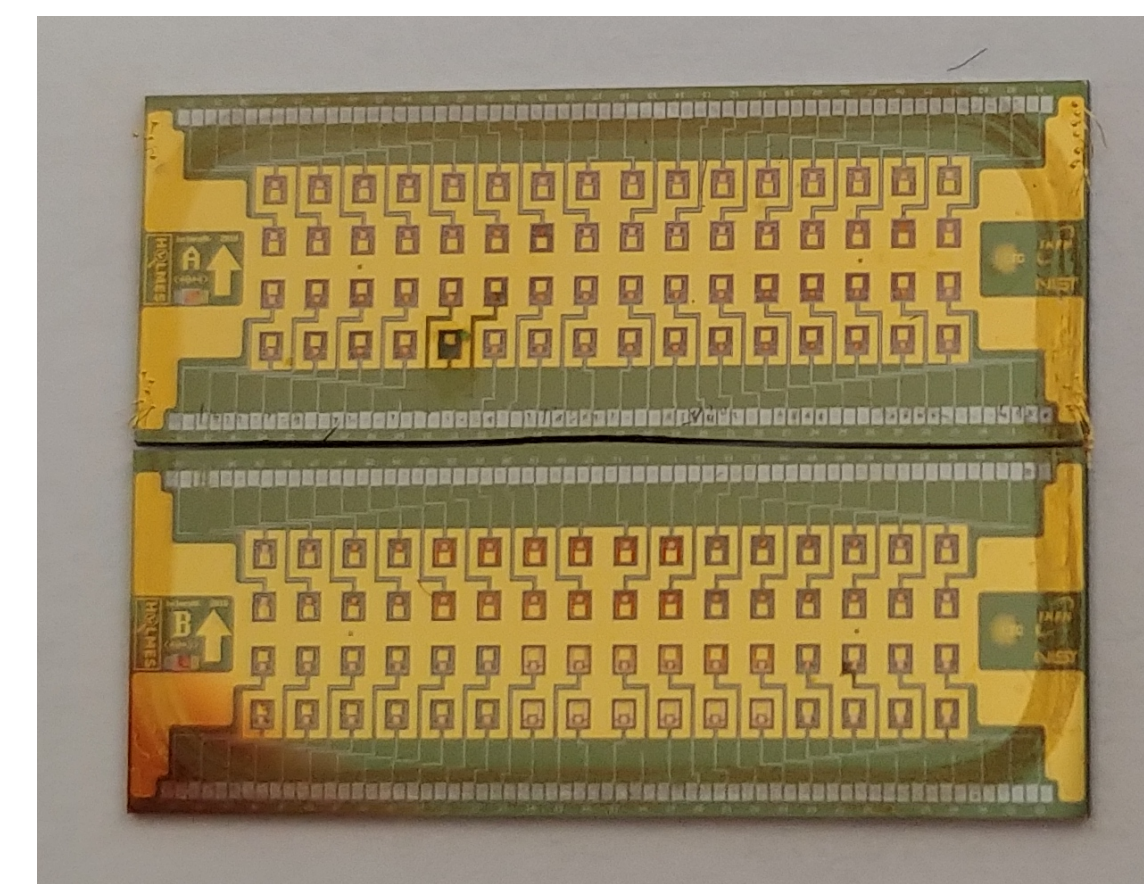
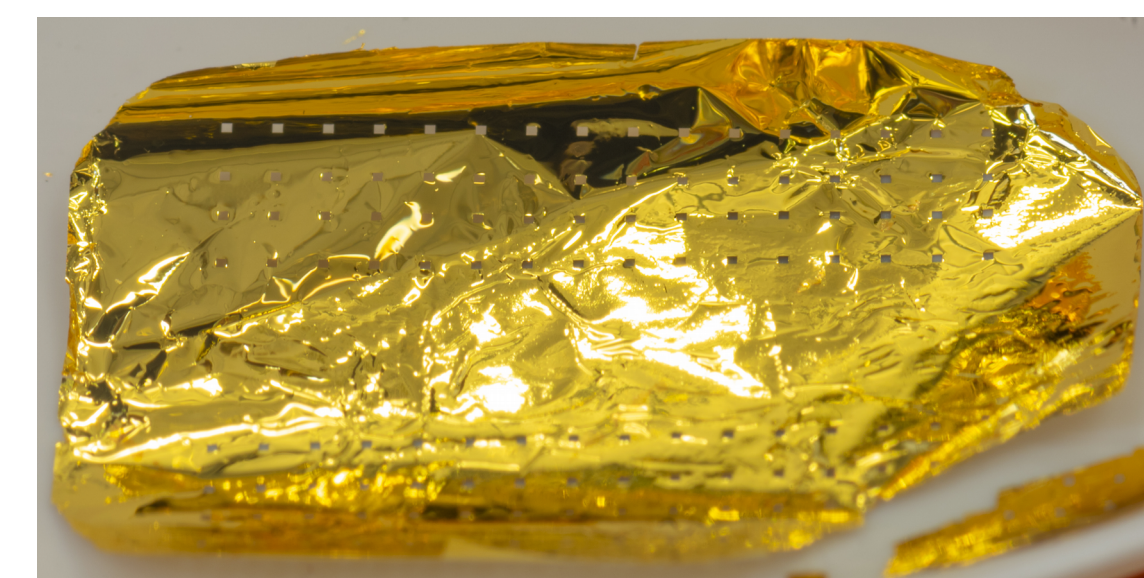
Zoom of a single absorber



Minimal crowning
Almost isotropical deposition thanks to
the 4 ion beam sources

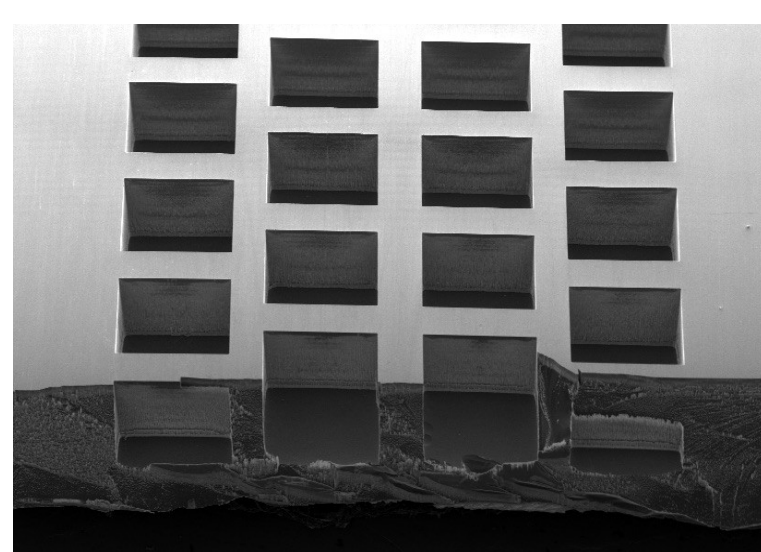
- Sample in acetone for 24 h
- Acetone @ 40°C

After the lift-off, the Au
dopisited remains only on the
Absorber

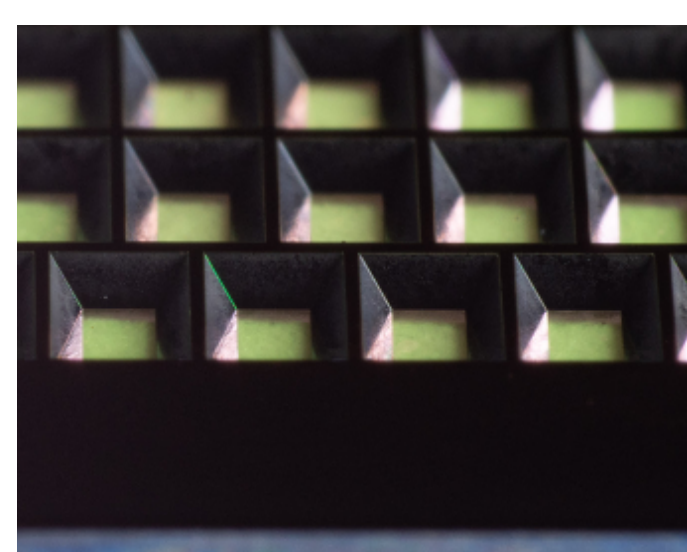


SiN membrane release

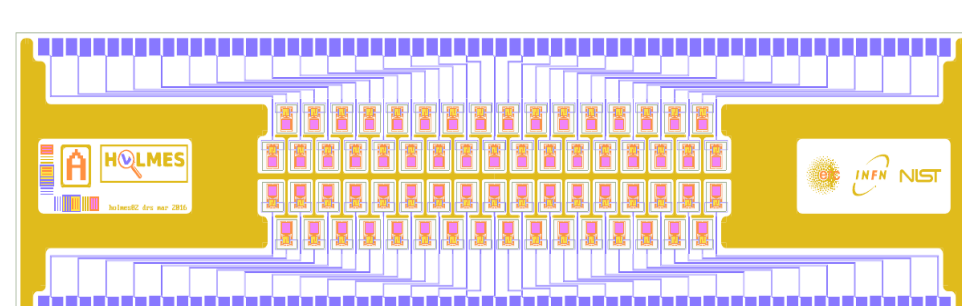
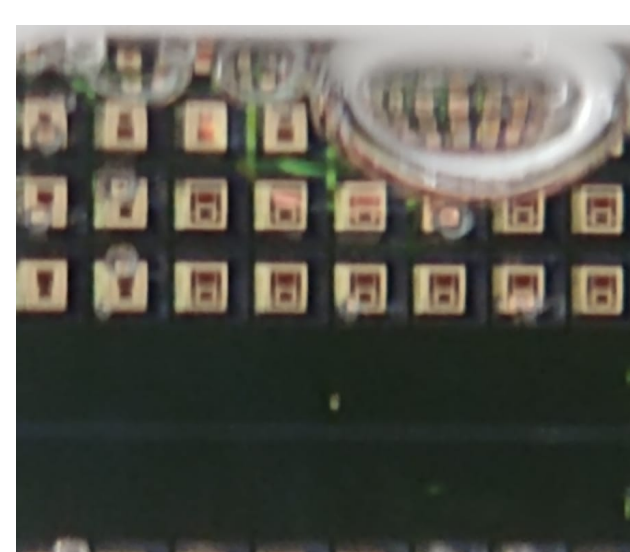
two options for membrane release (i.e. final array fabrication step)



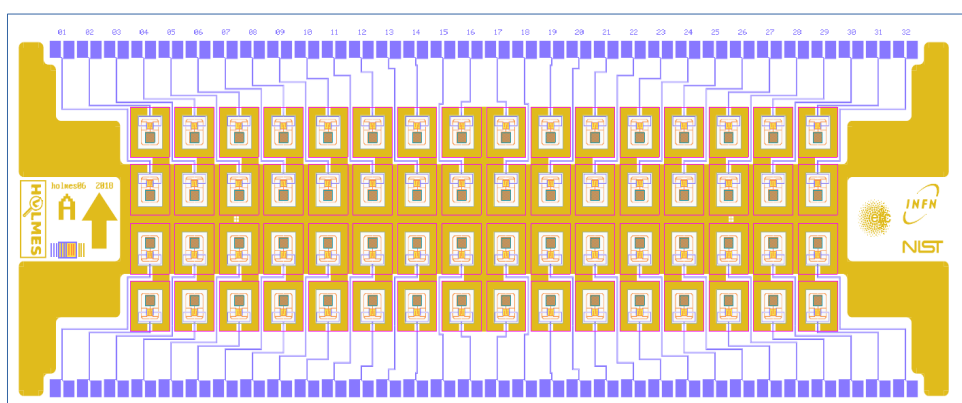
- Silicon Deep Reactive Ion Etching (DRIE)
- best for close packing and high implant efficiency
- not yet properly tuned \rightarrow work in progress



- Silicon KOH anisotropic wet etching
- requires more spacing between pixels
- succesfully tuned \rightarrow HOLMES baseline



calculated ^{163}Ho
beam FWHM width



In summary

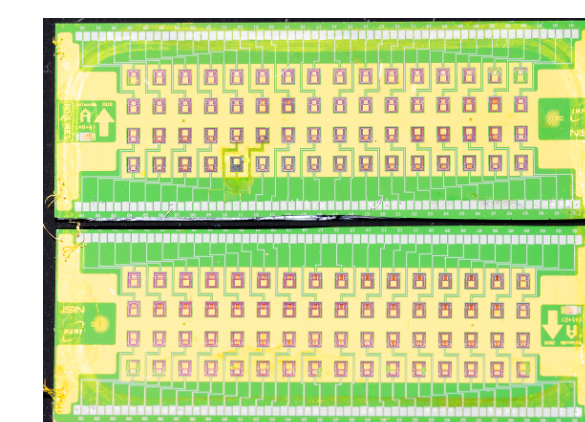
Deposition
of 1 μ m Au



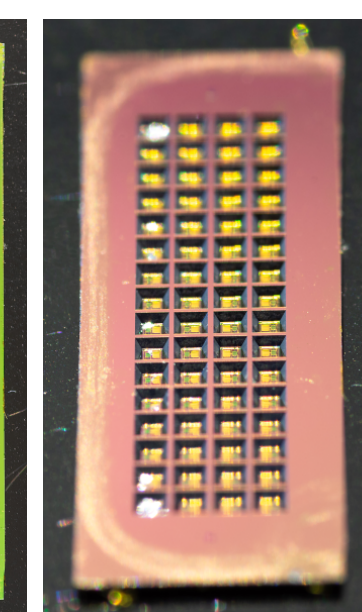
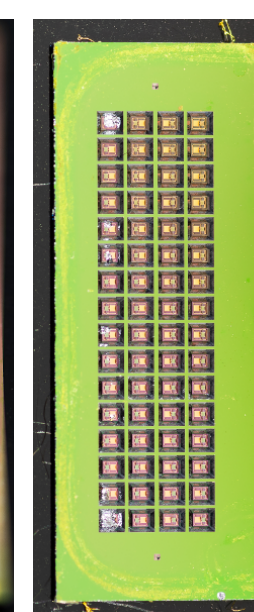
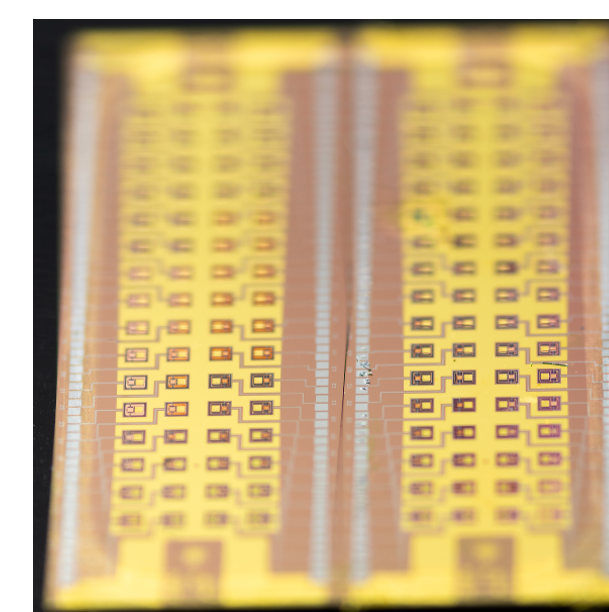
KOH
etching



Lift-off



Final result



The first
processed
HOLMES array
without ^{163}Ho is
in measurement
now!